4-by-4 Register File (with 3-state outputs)

# HITACHI

ADE-205-521 (Z) 1st. Edition Sep. 2000

### **Description**

The HD74HC670, 16-bit register file is organized as 4 words of 4 bits each and separate on-chip decoding is provided for addressing the four word locations to either write-in or retrieve data.

This permits simultaneous writing into one location and reading from another word location. Four data inputs are available which are used to supply the 4-bit word to be stored. Location of the word is determined by the write-address inputs A and B in conjunction with a write-enable signal. Data applied at the inputs should be in its true form. That is, if a high-level signal is desired from the output, a high-level is applied at the data input for that particular bit location. The latch inputs are arranged so that new data will be accepted only if both internal address gate inputs are high. When this condition exists, data at the D input is transferred to the latch output. When the write-enable input,  $(G_W)$  is high, the data inputs are inhibited and their levels can cuase no change in the information stored in the internal latches. When the read-enable input,  $(G_R)$  is high, the data outputs are inhibited and go into the high-impedance state. The individual address lines permit direct acquisition of data stored in any four of the latches. Four individual decoding gates are used to complete the address for reading a word. when the read address is made in conjunction with the read-enable signal, the word appears at the four outputs.

### **Features**

• High Speed Operation:  $t_{pd}$  (Read Select to Q) = 21 ns typ ( $C_L = 50$  pF)

• High Output Current: Fanout of 15 LSTTL Loads

• Wide Operating Voltage:  $V_{CC} = 2$  to 6 V

• Low Input Current: 1 μA max

• Low Quiescent Supply Current:  $I_{CC}$  (static) = 4  $\mu$ A max (Ta = 25°C)



### **Function Table**

Write Inputs			Word	Word							
W <sub>B</sub>	W <sub>A</sub>	G <sub>w</sub>	0	1	2	3					
L	L	L	Q = D	$Q_0$	$Q_0$	$Q_0$					
L	Н	L	$Q_0$	Q = D	$Q_0$	$Q_0$					
Н	L	L	$Q_0$	$Q_0$	Q = D	$Q_0$					
Н	Н	L	$Q_0$	$Q_0$	$Q_0$	Q = D					
X	Х	Н	$Q_0$	Q <sub>o</sub>	Q <sub>o</sub>	$Q_0$					

Read In	puts		Outputs				
R <sub>B</sub>	R <sub>A</sub>	<b>G</b> <sub>R</sub>	Q <sub>1</sub>	$Q_2$	$Q_{_3}$	$Q_4$	
L	L	L	$W_0 B_1$	$W_0 B_2$	$W_0 B_3$	$W_0 B_4$	
L	Н	L	W <sub>1</sub> B <sub>1</sub>	$W_1 B_2$	W <sub>1</sub> B <sub>3</sub>	W <sub>1</sub> B <sub>4</sub>	
Н	L	L	W <sub>2</sub> B <sub>1</sub>	$W_2 B_2$	$W_2 B_3$	$W_2 B_4$	
Н	Н	L	W <sub>3</sub> B <sub>1</sub>	$W_3 B_2$	$W_3 B_3$	$W_3 B_4$	
X	Х	Н	Z	Z	Z	Z	

H: high levelL: low levelX: irrelevant

Z: high impedance (off)

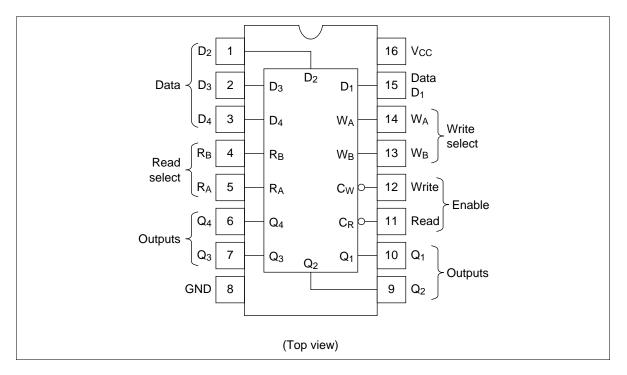
(Q = D): The four selected internal flip-flop outputs will assume the states applied to the four external data

inputs.

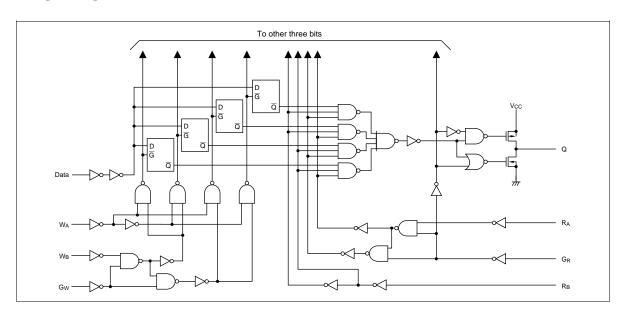
 $\mathbf{Q}_{\!\scriptscriptstyle 0}$  : The level of Q before the indicated input conditions were established.

 $W_0 B_1$ : The first bit of word 0, etc.

# Pin Arrangement



## Logic Diagram



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## **DC** Characteristics

			Ta = 25°C			Ta = -40 to +85°C				
Item	Symbol	V <sub>cc</sub> (V)	Min	Тур	Max	Min	Max	Unit	<b>Test Condition</b>	ns
Input voltage	V <sub>IH</sub>	2.0	1.5	_	_	1.5	_	V		
		4.5	3.15	_	_	3.15	_	_		
		6.0	4.2	_	_	4.2	_	_		
	V <sub>IL</sub>	2.0	_	_	0.5	_	0.5	V		
		4.5	_	_	1.35	_	1.35	=		
		6.0	_	_	1.8	_	1.8	_		
Output voltage	V <sub>OH</sub>	2.0	1.9	2.0	_	1.9	_	V	Vin = V <sub>IH</sub> or V <sub>IL</sub>	$I_{OH} = -20 \mu A$
		4.5	4.4	4.5	_	4.4	_	=		
		6.0	5.9	6.0	_	5.9	_	_		
		4.5	4.18	_	_	4.13	_	_		$I_{OH} = -6 \text{ mA}$
		6.0	5.68	_	_	5.63	_	=		$I_{OH} = -7.8 \text{ mA}$
	V <sub>OL</sub>	2.0	_	0.0	0.1	_	0.1	V	Vin = V <sub>IH</sub> or V <sub>IL</sub>	I <sub>OL</sub> = 20 μA
		4.5	_	0.0	0.1	_	0.1	_		
		6.0	_	0.0	0.1	_	0.1	_		
		4.5	_	_	0.26	_	0.33	_		$I_{OL} = 6 \text{ mA}$
		6.0	_	_	0.26	_	0.33	_		I <sub>OL</sub> = 7.8 mA
Off-state output current	l <sub>oz</sub>	6.0	_	_	±0.5	_	±5.0	μΑ	$Vin = V_{IN} \text{ or } V_{IL},$ $Vout = V_{CC} \text{ or } G$	SND
Input current	lin	6.0	_	_	±0.1	_	±1.0	μΑ	Vin = V <sub>CC</sub> or GN	ID
Quiescent supply current	I <sub>cc</sub>	6.0	_	_	4.0	_	40	μΑ	$Vin = V_{CC} \text{ or } GN$	ID, lout = $0 \mu A$

**AC Characteristics** ( $C_L = 50 \text{ pF}$ , Input  $t_r = t_f = 6 \text{ ns}$ )

Ta = -40 to  $Ta = 25^{\circ}C$  +85°C

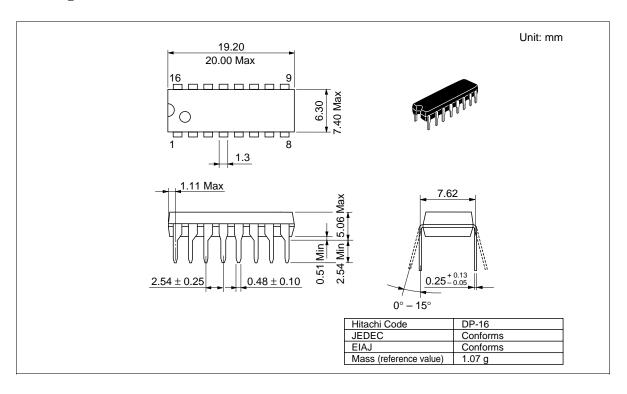
		V <sub>cc</sub> (V)	1a = 25°C			+85°C				
Item	Symbol		Min	Тур	Max	Min	Max	Unit	Test Conditions	
Propagation delay	t <sub>PLH</sub>	2.0	_	_	160	_	200	ns	Read select to Q	
time	$t_{\tiny PHL}$	4.5	_	21	32	_	40	=		
		6.0	_	_	27	_	34	=		
	t <sub>PLH</sub>	2.0	_	_	200	_	250	ns	Write enable to Q	
	$t_{\tiny PHL}$	4.5	_	24	40	_	50	=		
		6.0	_	_	34	_	43	=		
	t <sub>PLH</sub>	2.0	_	_	150	_	190	ns	Data to Q	
	$t_{\tiny PHL}$	4.5	_	18	30	_	38	=		
		6.0	_	_	26	_	33	=		
Output enable	t <sub>zH</sub>	2.0	_	_	150	_	190	ns		
time	$t_{ZL}$	4.5	_	18	30	_	38	-		
		6.0	_	_	26	_	33	_		
Output disable	t <sub>HZ</sub>	2.0	_	_	150	_	190	ns		
time	$t_{LZ}$	4.5	_	17	30	_	38	-		
		6.0	_	_	26	_	33	_		
Pulse width	t <sub>w</sub>	2.0	80	_	_	100	_	ns		
		4.5	16	_	_	20	_	=		
		6.0	14	_	_	17	_	=		
Setup time	t <sub>su</sub>	2.0	60	_	_	75	_	ns	Data to Write enable	
		4.5	12	4	_	15	_	=		
		6.0	10	_	_	13	_	-		
	t <sub>su</sub>	2.0	60	_	_	75	_	ns	Write select to Write enable	
		4.5	12	_	_	15	_	-		
		6.0	10	_	_	13	_	-		
Hold time	t <sub>h</sub>	2.0	50	_	_	63	_	ns	Write enable to Data	
		4.5	10	6	_	13	_	-		
		6.0	9	_	_	11	_	-		
		2.0	50	_	_	63	_	ns	Write enable to Write select	
		4.5	10	_	_	13	_	_		
		6.0	9	_	_	11	_	=		

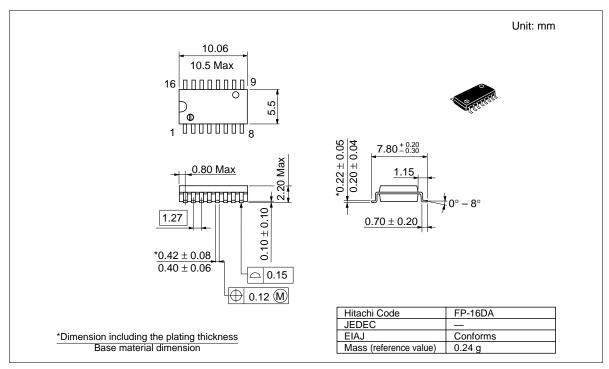
AC Characteristics ( $C_L = 50 \text{ pF}$ , Input  $t_r = t_f = 6 \text{ ns}$ ) (cont)

			Ta = 25°C		+85°C				
Item	Symbol	V <sub>cc</sub> (V)	Min	Тур	Max	Min	Max	Unit	Test Conditions
Latch time for new	t <sub>latch</sub>	2.5	100	_	_	125	_	ns	
data		4.5	20	_	_	25	_	_	
		6.0	17	_	_	21	_	_	
Output rise/fall	t <sub>TLH</sub>	2.0	_	_	75	_	95	ns	
time	$\mathbf{t}_{THL}$	4.5	_	5	15	_	19	_	
		6.0	_	_	13	_	16	_	
Input capacitance	Cin	_	_	5	10	_	10	pF	

Ta = -40 to

### **Package Dimensions**





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